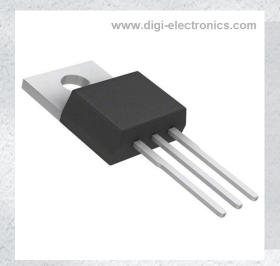


# FJP1943RTU Datasheet



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DiGi Electronics Part Number FJP1943RTU-DG

Manufacturer onsemi

Manufacturer Product Number FJP1943RTU

Description TRANS PNP 230V 15A TO220-3

Detailed Description Bipolar (BJT) Transistor PNP 230 V 15 A 30MHz 80 W

Through Hole TO-220-3



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RFQ Email: Info@DiGi-Electronics.com

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## **Purchase and inquiry**

| Manufacturer Product Number:                 | Manufacturer:                          |
|--|--|
| FJP1943RTU                                   | onsemi                                 |
| Series:                                      | Product Status:                        |
|  | Obsolete                               |
| Transistor Type:                             | Current - Collector (Ic) (Max):        |
| PNP  | 15 A                                   |
| Voltage - Collector Emitter Breakdown (Max): | Vce Saturation (Max) @ lb, lc:         |
| 230 V  | 3V @ 800mA, 8A                         |
| Current - Collector Cutoff (Max):            | DC Current Gain (hFE) (Min) @ Ic, Vce: |
| 5μA (ICBO)                                   | 55 @ 1A, 5V                            |
| Power - Max:                                 | Frequency - Transition:                |
| 80 W   | 30MHz                                  |
| Operating Temperature:                       | Mounting Type:                         |
| -50°C ~ 150°C (TJ)                           | Through Hole                           |
| Package / Case:                              | Supplier Device Package:               |
| TO-220-3                                     | TO-220-3                               |
| Base Product Number:                         |  |
| FJP1943                                      |  |

## **Environmental & Export classification**

| RoHS Status:     | Moisture Sensitivity Level (MSL): |
|------------------|-----------------------------------|
| ROHS3 Compliant  | Not Applicable                    |
| REACH Status:    | ECCN:                             |
| REACH Unaffected | EAR99                             |
| HTSUS:           |                                   |
| 8541.29.0075     |                                   |



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November 2008

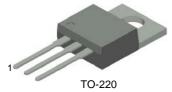
# FJP1943 PNP Epitaxial Silicon Transistor

#### **Applications**

- · High-Fidelity Audio Output Amplifier
- · General Purpose Power Amplifier

#### **Features**

- High Current Capability: I<sub>C</sub> = -15A.
- High Power Dissipation: 80watts.
- High Frequency: 30MHz.
- High Voltage : V<sub>CEO</sub>= -230V
- · Wide S.O.A for reliable operation.
- · Excellent Gain Linearity for low THD.
- Complement to FJP5200
- Full thermal and electrical Spice models are available.
- · Same transistor is also available in:
  - -- TO264 package, 2SA1943/FJL4215 : 150 watts
  - -- TO3P package, 2SA1962/FJA4213: 130 watts
  - -- TO220F package, FJPF1943: 50 watts



1.Base 2.Collector 3.Emitter

#### Absolute Maximum Ratings\* Ta = 25°C unless otherwise noted

| Symbol                            | Parameter  | Ratings     | Units     |  |
|-----------------------------------|--|-------------|-----------|--|
| BV <sub>CBO</sub>                 | Collector-Base Voltage   | -230        | V         |  |
| BV <sub>CEO</sub>                 | Collector-Emitter Voltage  | -230        | V         |  |
| BV <sub>EBO</sub>                 | Emitter-Base Voltage   | -5          | V         |  |
| I <sub>C</sub>                    | Collector Current  | -15         | А         |  |
| I <sub>B</sub>                    | Base Current   | -1.5        | А         |  |
| P <sub>D</sub>                    | Total Device Dissipation(T <sub>C</sub> =25°C) Derate above 25°C | 80<br>0.64  | W<br>W/°C |  |
| T <sub>J</sub> , T <sub>STG</sub> | Junction and Storage Temperature                                 | - 50 ~ +150 | °C        |  |

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### $\textbf{Thermal Characteristics*} \quad \textbf{T}_{a} = 25 ^{\circ} \textbf{C} \text{ unless otherwise noted}$

| Symbol         | Parameter                            | Ratings | Units |
|----------------|--------------------------------------|---------|-------|
| $R_{	heta JC}$ | Thermal Resistance, Junction to Case | 1.25    | °C/W  |

<sup>\*</sup> Device mounted on minimum pad size

#### **h**<sub>FE</sub> Classification

| Classification   | R        | 0        |
|------------------|----------|----------|
| h <sub>FE1</sub> | 55 ~ 110 | 80 ~ 160 |

#### **Electrical Characteristics\*** T<sub>a</sub>=25°C unless otherwise noted

| Symbol                | Parameter                            | Test Condition                             | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | I <sub>C</sub> =-5mA, I <sub>E</sub> =0    | -230 |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =-10mA, R <sub>BE</sub> =∞  | -230 |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | I <sub>E</sub> =-5mA, I <sub>C</sub> =0    | -5   |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | V <sub>CB</sub> =-230V, I <sub>E</sub> =0  |      |      | -5.0 | μА    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | V <sub>EB</sub> =-5V, I <sub>C</sub> =0    |      |      | -5.0 | μΑ    |
| h <sub>FE1</sub>      | DC Current Gain                      | V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A  | 55   |      | 160  |       |
| h <sub>FE2</sub>      | DC Current Gain                      | V <sub>CE</sub> =-5V, I <sub>C</sub> =-7A  | 35   | 60   |      |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =-8A, I <sub>B</sub> =-0.8A |      | -0.4 | -3.0 | V     |
| V <sub>BE</sub> (on)  | Base-Emitter On Voltage              | V <sub>CE</sub> =-5V, I <sub>C</sub> =-7A  |      | -1.0 | -1.5 | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A  |      | 30   |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =-10V, f=1MHz              |      | 360  |      | pF    |

<sup>\*</sup> Pulse Test: Pulse Widt=20μs, Duty Cycle≤2%

#### **Ordering Information**

| Part Number | Marking | Package | Packing Method | Remarks      |
|-------------|---------|---------|----------------|--------------|
| FJP1943RTU  | J1943R  | TO-220  | TUBE           | hFE1 R grade |
| FJP1943OTU  | J1943O  | TO-220  | TUBE           | hFE1 O grade |

#### **Typical Characteristics**

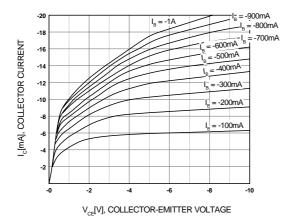


Figure 1. Static Characteristic

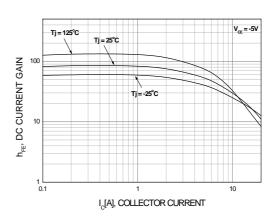


Figure 2. DC current Gain ( R Grade )

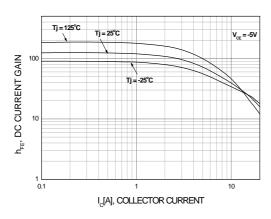


Figure 3. DC current Gain (O Grade)

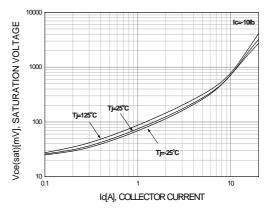


Figure 4. Collector-Emitter Saturation Voltage

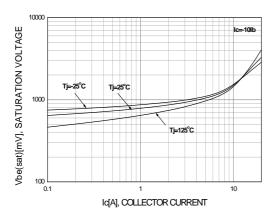


Figure 5. Base-Emitter Saturation Voltage

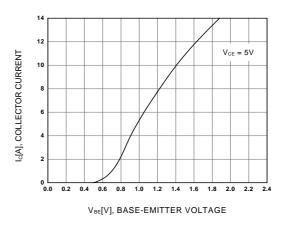


Figure 6. Base-Emitter On Voltage

# **Typical Characteristics**

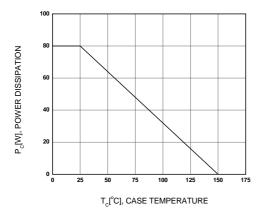


Figure 7. Power Derating

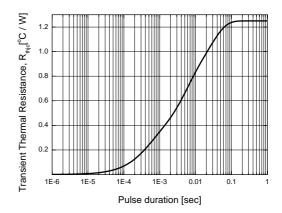
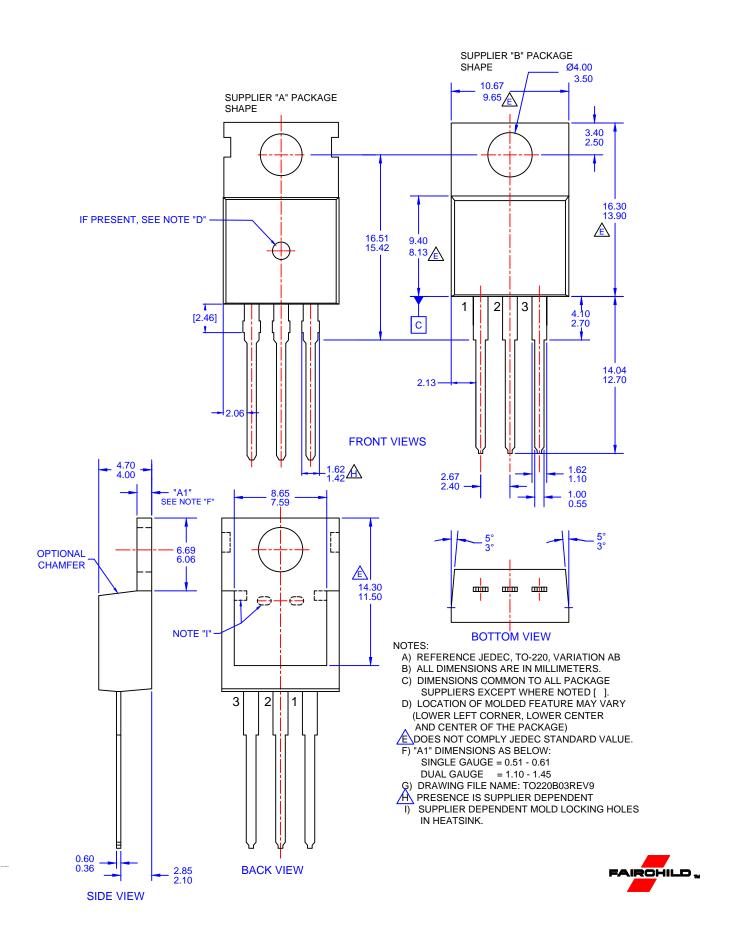


Figure 8. Thermal Resistance



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